



# 100V NPN MEDIUM POWER LOW SATURATION TRANSISTOR POWERDI®5

#### **Features**

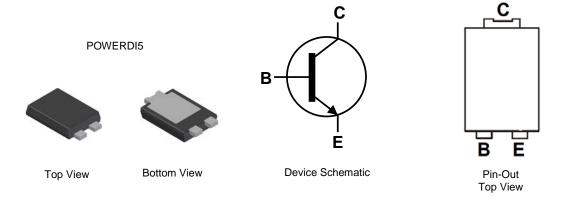
- BV<sub>CEO</sub> > 100V
- I<sub>C</sub> = 6A High Continuous Collector Current
- I<sub>CM</sub> = 10A Peak Collector Current
- P<sub>D</sub> up to 3.2W
- 43% smaller than SOT223; 60% smaller than TO252
- Maximum height just 1.1mm
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: PowerDI5
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 <sup>®</sup>
- Weight: 0.093 grams (approximate)

#### **Applications**

- Motor Drive
- Voltage Regulator using Emitter-Follower
- DC-DC Converter
- Telecoms
- Power Management



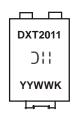
#### Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DXT2011P5-13	AEC-Q101	DXT2011	13	16	5,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



DXT2011 = Product Type Marking Code

| | = Manufacturers' Code Marking

K = Factory Designator

YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 09 for 2009)

WW = Week code (01 to 53)





# **Absolute Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	200	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	Ic	6	А
Peak Pulse Current	I <sub>CM</sub>	10	Α

#### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit			
	(Note 5)		3.2			
Power Dissipation	(Note 6)	$P_{D}$	1.7	W		
	(Note 7)		0.74			
	(Note 5)		39			
Thermal Resistance, Junction to Ambient Air	(Note 6)	$R_{ heta JA}$	75	0000		
	(Note 7)		169	°C/W		
Thermal Resistance, Junction to Leads (Note 8)		$R_{ heta JL}$	5.6			
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C			

# ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with the exposed collector pad on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

  6. Same as note (5), except mounted on 25mm x 25mm 1oz copper.

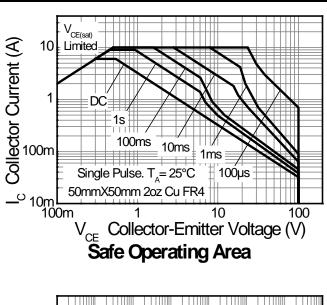
  7. Same as note (5), except mounted on minimum recommended pad (MRP) layout.

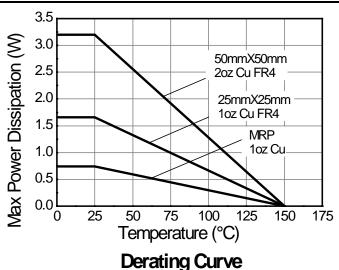
  8. Thermal resistance from junction to solder-point (on the exposed collector pad).

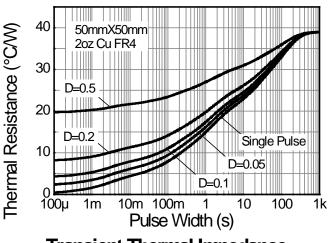
  9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

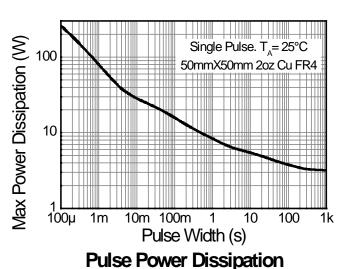


### Thermal Characteristics and Derating Information









**Transient Thermal Impedance** 

180 Thermal Resistance (°C/W)  $T_{\Delta} = 25^{\circ}C$ 160 Power Rating (W) 140 1 oz. weight Copper 120 100 80 60 2 oz. weight Copper 40 20 L 10 100 1000 10000 Copper Area (sq mm)

T<sub>A</sub>= 25°C

2 oz. weight Copper

1 oz. weight Copper

1 oz. weight Copper

Copper Area (sq mm)

Thermal Resistance vs. Cu Area

Power Rating vs. Cu Area





**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

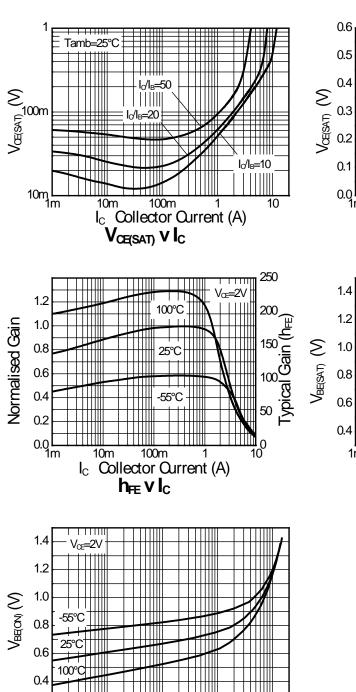
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	200	235	_	>	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV <sub>CEO</sub>	100	115	_	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8.1	_	V	$I_E = 100 \mu A$
Collector Cutoff Current	I <sub>CBO</sub>	1 1	_	20 0.5	nΑ μΑ	V <sub>CB</sub> = 150V V <sub>CB</sub> = 150V, T <sub>AMB</sub> = 100°C
Collector Cutoff Current	I <sub>CER</sub> R≤1kΩ		_ _	20 0.5	nΑ μΑ	V <sub>CB</sub> = 150V V <sub>CB</sub> = 150V, T <sub>AMB</sub> = 100°C
Emitter Cutoff Current	I <sub>EBO</sub>	_		10	nA	V <sub>EB</sub> = 6V
Collector-Emitter Saturation Voltage (Note 10)	V <sub>CE(sat)</sub>	_ _ _	21 50 95 180	35 65 125 220	mV	$I_C = 0.1A$ , $I_B = -5mA$ $I_C = 1A$ , $I_B = 100mA$ $I_C = 2A$ , $I_B = 100mA$ $I_C = 5A$ , $I_B = 500mA$
Base-Emitter Saturation Voltage (Note 10)	V <sub>BE(sat)</sub>	_	1020	1120	mV	$I_C = 5A$ , $I_B = 500mA$
Base-Emitter Turn-On Voltage (Note 10)	V <sub>BE(on)</sub>	_	920	1000	mV	$V_{CE} = 2V$ , $I_C = 5A$
DC Current Gain (Note 10)	h <sub>FE</sub>	100 100 30 10	_ _ _	300 — —	_	V <sub>CE</sub> = 2V, I <sub>C</sub> = 10mA V <sub>CE</sub> = 2V, I <sub>C</sub> = 2A V <sub>CE</sub> = 2V, I <sub>C</sub> = 5A V <sub>CE</sub> = 2V, I <sub>C</sub> = 10A
Transition Frequency	f <sub>T</sub>	1	130	_	MHz	V <sub>CE</sub> = 10V, I <sub>C</sub> = 100mA, f = 50MHz
Output Capacitance	C <sub>obo</sub>		26	_	pF	V <sub>CB</sub> = 10V, f = 1MHz
Switching Times	t <sub>on</sub> t <sub>off</sub>	_ _	41 1010	_ _	ns	$V_{CC} = 10V, I_C = 1A,$ $I_{B1} = I_{B2} = 100mA$

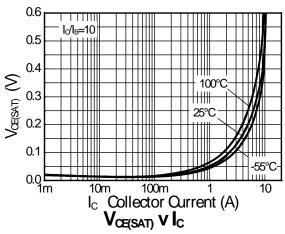
Note: 10. Pulse Test: Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2.0%.

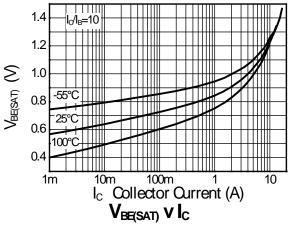




### Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)



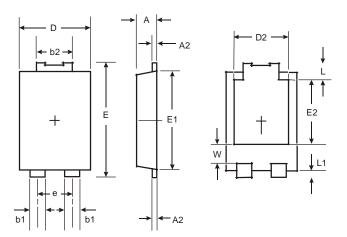






# **Package Outline Dimensions**

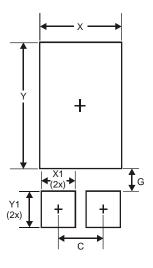
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



POWERDI5					
Dim	Min Max				
Α	1.05	1.15			
A2	0.33	0.43			
b1	0.80	0.99			
b2	1.70	1.88			
D	3.90	4.05			
D2	3.054 Typ				
Е	6.40	6.60			
е	1.84 Typ				
E1	5.30	5.45			
E2	3.549 Typ				
L	0.75 0.95				
L1	0.50 0.65				
W	1.10	1.41			
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	1.840
G	0.852
Х	3.360
X1	1.390
Υ	4.860
Y1	1.400

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.





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